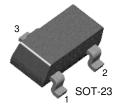


SEMICONDUCTOR®

KST05/06

Driver Transistor

- Collector-Emitter Voltage: V_{CEO} = KST05: 60V
- KST06: 80V
- Collector Power Dissipation: P_C (max) = 350mW
- Complement to KST55/56



1. Base 2. Emitter 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collecto-Base Voltage		
	: KST05	60	V
	: KST06	80	V
V _{CEO}	Collector-Emitter Voltage		
020	: KST05	60	V
	: KST06	80	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current	500	mA
P _C	Collector Power Dissipation	350	mW
T _{STG}	Storage Temperature	150	°C
R _{TH} (j-a)	Thermal Resistance junction to Ambient	357	°C/W

Electrical Characteristics Ta=25°C unless otherwise noted

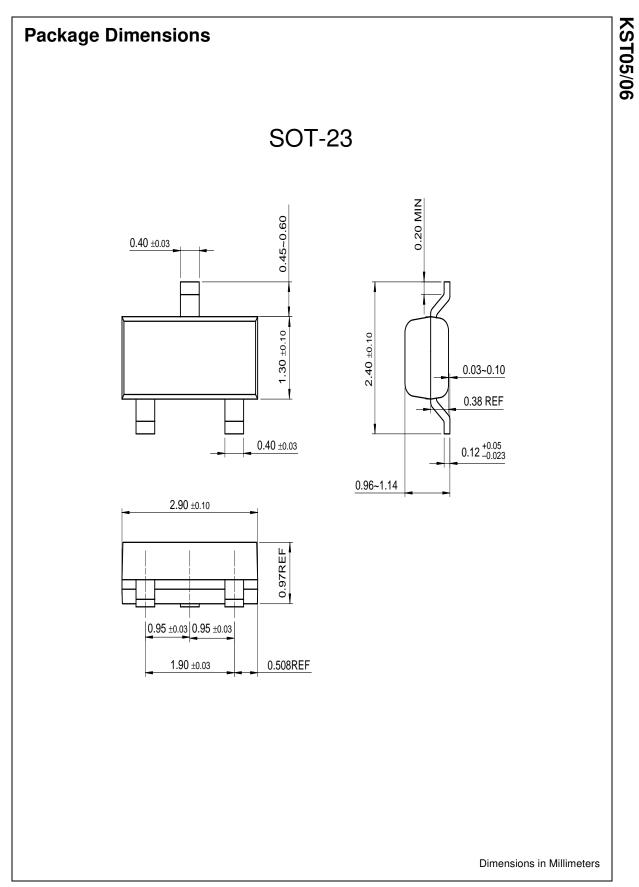
Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CEO}	* Collector-Emitter Breakdown Voltage : KST05 : KST06	I _C =1mA, I _B =0	60 80		V V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =100μA, I _C =0	4		V
I _{CBO}	Collector Cut-off Current : KST05 : KST06	V_{CB} =60V, I _E =0 V_{CB} =80V, I _E =0		0.1 0.1	μΑ μΑ
I _{CEO}	Collector Cut-off Current	V _{CE} =60V, I _B =0		0.1	μA
h _{FE}	DC Current Gain	V _{CE} =1V, I _C =10mA V _{CE} =1V, I _C =100mA	50 50		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =100mA, I _B =10mA		0.25	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =1V, I _C =100mA		1.2	V
f _T	Current Gain Bandwidth Product	V _{CE} =2V, I _C =100mA, f=100MHz	100		MHz

* Pulse Test: PW≤300μs, Duty Cycle≤2%

Marking Code

Туре	KST05	KST06
Mark	1H	1G





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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.